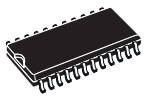
HCF4515B

OUTPUT "LOW" ON SELECT 4-BIT LATCH/4-TO-16 LINE DECODER

- QUIESCENT CURRENT SPECIF. UP TO 20V
- STROBED INPUT LATCH
- INHIBIT CONTROL
- INPUT LEAKAGE CURRENT I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



SOP

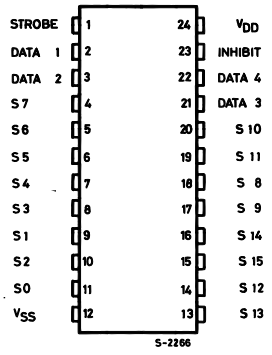
ORDER CODES

PACKAGE	TUBE	T & R
SOP	HCF4515BM1	HCF4515M013TR

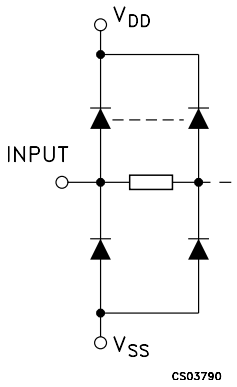
DESCRIPTION

HCF4515B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in SOP package.
HCF4515B consists of a 4-bit strobed latch and a 4 to 16 line decoder. The latches hold the last input data presented prior to the strobe transition from 1 to 0. Inhibit control allows all outputs to be placed at 1 regardless of the state of the data or strobe inputs. The decode truth table indicates all combinations of data inputs and appropriate selected outputs.

PIN CONNECTION



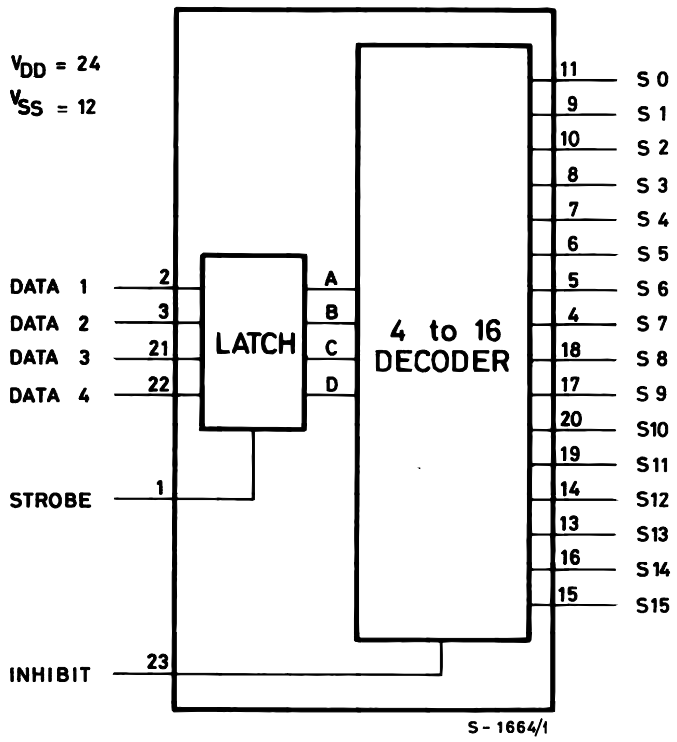
IINPUT EQUIVALENT CIRCUIT



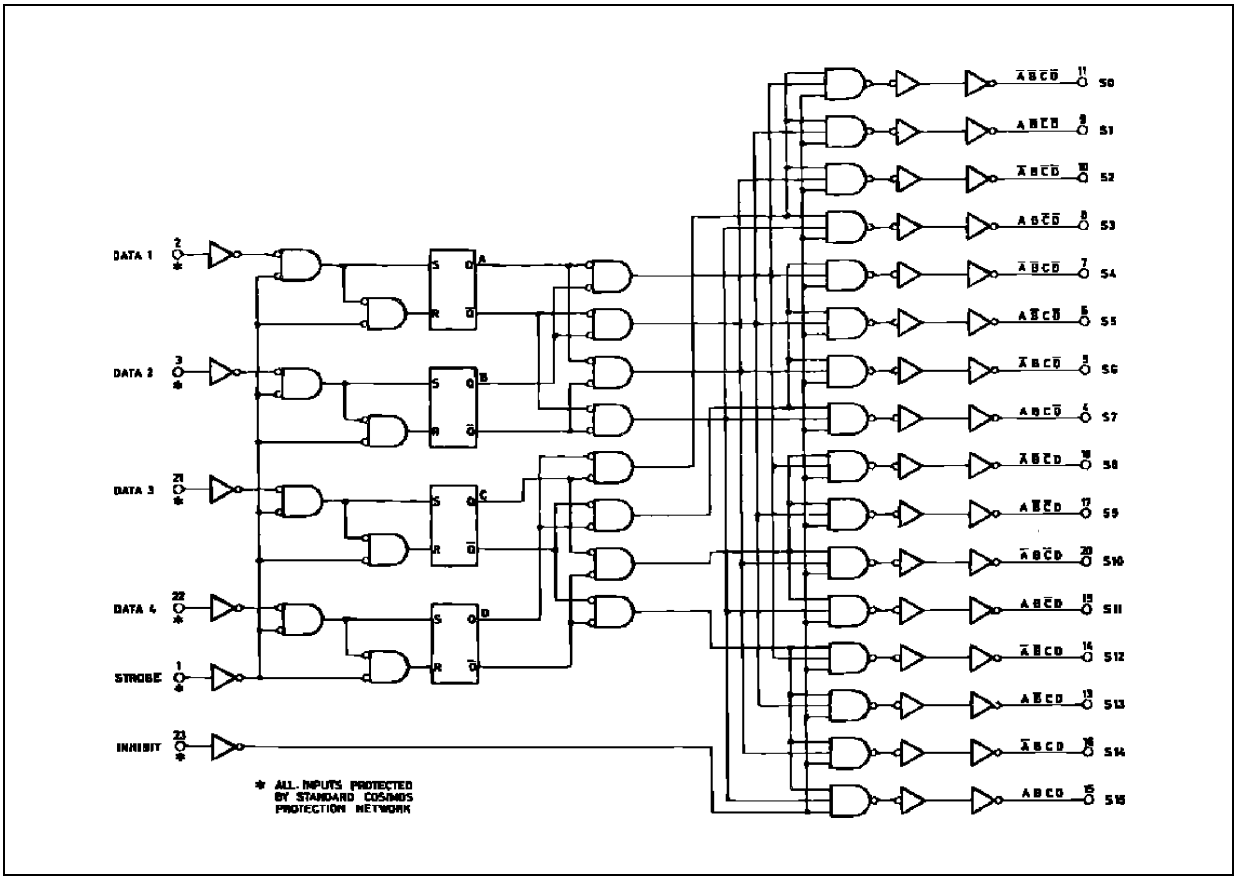
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	STROBE	Strobe Input
2, 3, 21, 22	DATA 1 to 4	Address Inputs
11, 9, 10, 8, 7, 6, 5, 4, 18, 17, 20, 19, 14, 13, 16, 15	S0 to S15	Multiplexer Outputs (Active HIGH)
23	INHIBIT	Enable Input
12	V_{SS}	Negative Supply Voltage
24	V_{DD}	Positive Supply Voltage

FUNCTIONAL DIAGRAM



LOGIC DIAGRAM



TRUTH TABLE

INPUTS					STROBE	SELECT OUTPUT
INHIBIT	A	B	C	D		
L	L	L	L	L	STROBE = "H" Refer to truth table	S0
L	H	L	L	L		S1
L	L	H	L	L		S2
L	H	H	L	L	STROBE = "L" Data at the negative going transition of strobe shall be provided on the each output while strobe is held low.	S3
L	L	L	H	L		S4
L	H	L	H	L		S5
L	L	H	H	L		S6
L	H	H	H	L		S7
L	L	L	L	H		S8
L	H	L	L	H		S9
L	L	H	L	H		S10
L	H	H	L	H		S11
L	L	L	H	H		S12
L	H	L	H	H		S13
L	L	H	H	H		S14
L	H	H	H	H		S15
H	X	X	X	X		ALL OUTPUTS "L"

X : Don't Care

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +22	V
V_I	DC Input Voltage	-0.5 to V_{DD} + 0.5	V
I_I	DC Input Current	± 10	mA
P_D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T_{op}	Operating Temperature	-55 to +125	°C
T_{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 20	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value							Unit
		V_I (V)	V_O (V)	$\|I_O\|$ (μA)	V_{DD} (V)	T_A = 25°C			-40 to 85°C		-55 to 125°C		
						Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
I_L	Quiescent Current	0/5			5		0.04	5		150		150	μA
		0/10			10		0.04	10		300		300	
		0/15			15		0.04	20		600		600	
		0/20			20		0.08	100		3000		3000	
V_{OH}	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
V_{OL}	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
V_{IH}	High Level Input Voltage		0.5/4.5	<1	5	3.5			3.5		3.5		V
			1/9	<1	10	7			7		7		
			1.5/13.5	<1	15	11			11		11		
V_{IL}	Low Level Input Voltage		4.5/0.5	<1	5			1.5		1.5		1.5	V
			9/1	<1	10			3		3		3	
			13.5/1.5	<1	15			4		4		4	
I_{OH}	Output Drive Current	0/5	2.5	<1	5	-1.36	-3.2		-1.1		-1.1		mA
		0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I_{OL}	Output Sink Current	0/5	0.4	<1	5	0.44	1		0.36		0.36		mA
		0/10	0.5	<1	10	1.1	2.6		0.9		0.9		
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I_I	Input Leakage Current	0/18	Any Input		18		$\pm 10^{-5}$	±0.1		±1		±1	μA
C_I	Input Capacitance		Any Input				5	7.5					pF

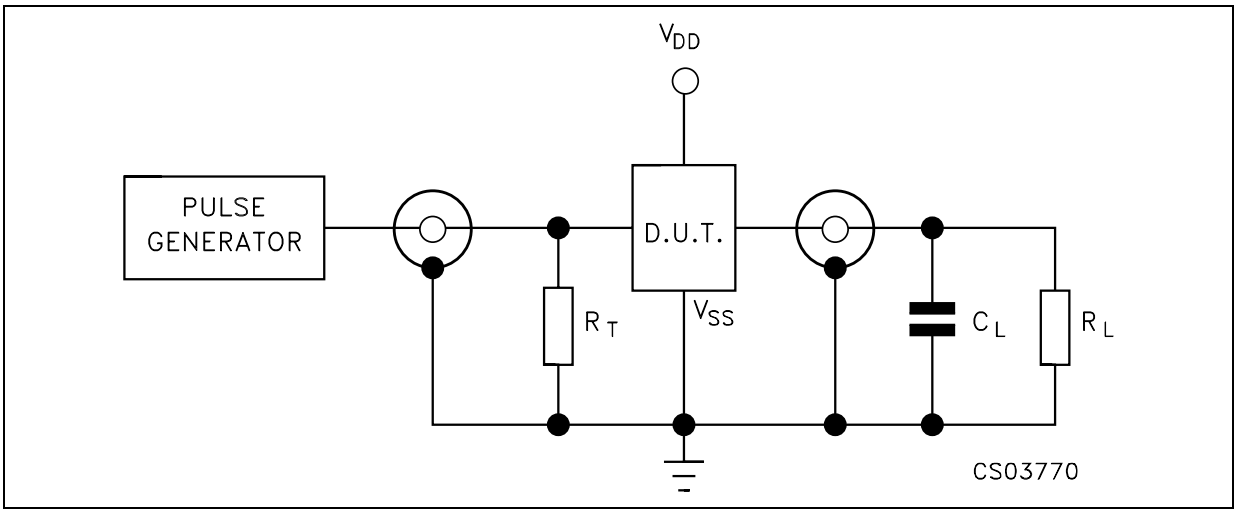
The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD}=5V, 2V min. with V_{DD}=10V, 2.5V min. with V_{DD}=15V

DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200KΩ, $t_r = t_f$ = 20 ns)

Symbol	Parameter	Test Condition		Value (*)			Unit
		V_{DD} (V)		Min.	Typ.	Max.	
t_{PHL} t_{PLH}	Propagation Delay Time	5	Strobe or Data		485	970	ns
		10			185	370	
		15			135	270	
t_{PHL} t_{PLH}	Propagation Delay Time	5	Inhibit		250	500	ns
		10			110	220	
		15			85	170	
t_{THL} t_{TLH}	Transition Time	5			100	200	ns
		10			50	100	
		15			40	80	
t_W	Strobe Pulse Width	5		250	125		ns
		10		100	50		
		15		70	35		
t_{setup}	Setup Time	5		150	75		ns
		10		70	35		
		15		40	20		

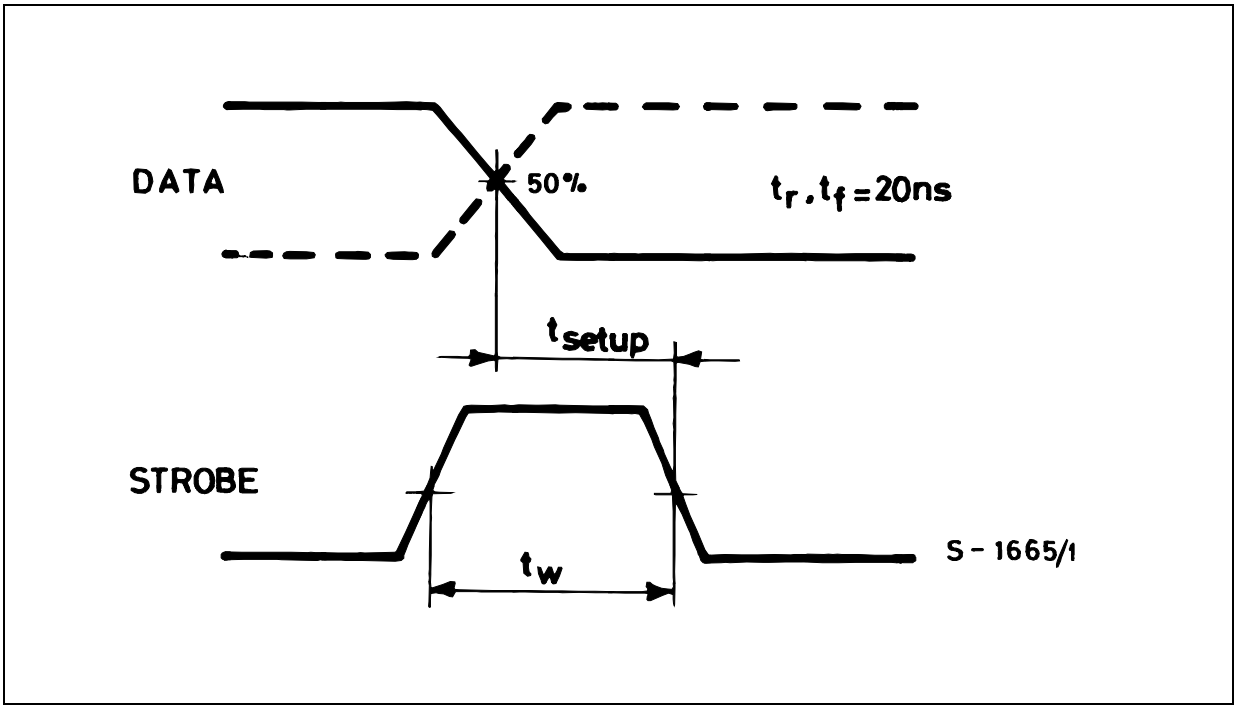
(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/°C
(1) : If more than one unit is cascaded. tr should be made less than or equal to the sum of the transition time and the fixed propagation delay of the output of the driving stage for the estimated capacitive load.

TEST CIRCUIT



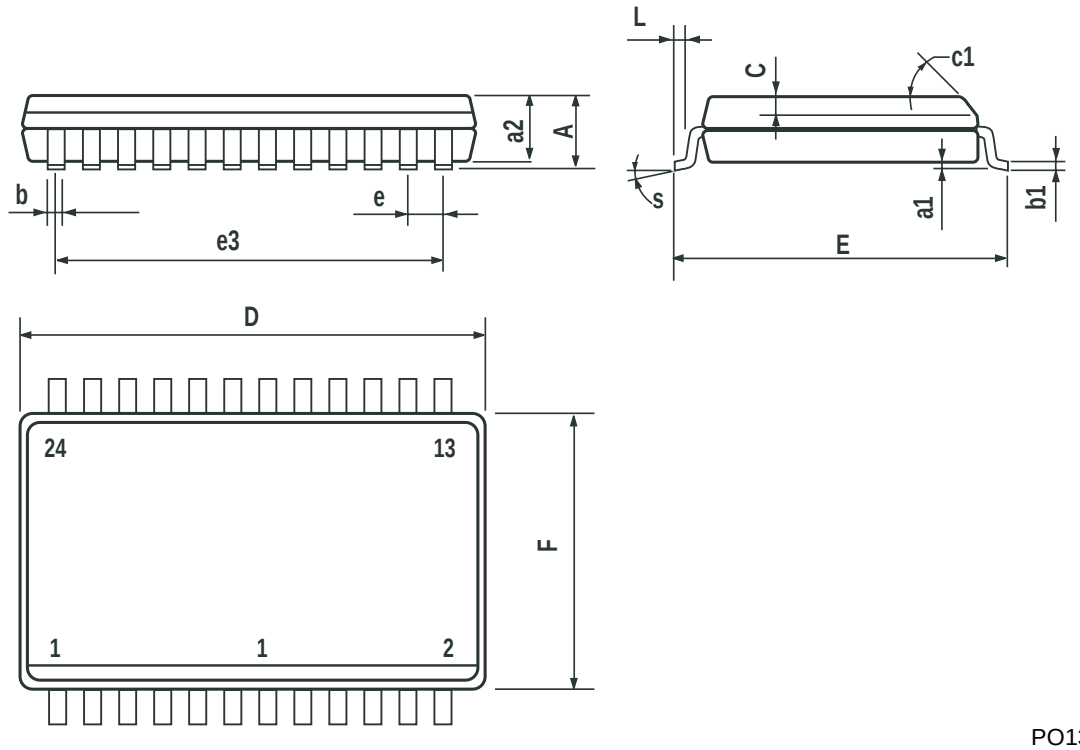
C_L = 50pF or equivalent (includes jig and probe capacitance)
R_L = 200KΩ
$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM : SETUP TIME and STROBE PULSE WIDTH (f=1MHz; 50% duty cycle)



SO-24 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.012
C		0.5			0.020	
c1	45° (typ.)					
D	15.20		15.60	0.598		0.614
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		13.97			0.550	
F	7.40		7.60	0.291		0.300
L	0.50		1.27	0.020		0.050
S	8° (max.)					



PO13T